

SKiiP® 2

2-pack - integrated intelligent Power System

Power section

SKiiP 432GB120-207CTV

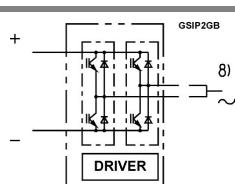
Features

- SKiiP technology inside
- Low loss IGBTs
- CAL diode technology
- Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP® 2 System)
- IEC 68T.1 (climate) 40/125/56 (SKiiP® 2 power section)

- 1) with assembly of suitable MKP capacitor per terminal (SEMIKRON type is recommended)
- 2) AC connection busbars must be connected by the user; copper busbars available on request

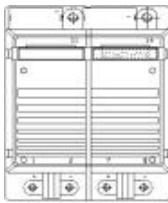
Absolute Maximum Ratings		$T_s = 25 \text{ }^\circ\text{C}$ unless otherwise specified		
Symbol	Conditions	Values		Units
IGBT				
V_{CES}		1200		V
$V_{CC}^1)$	Operating DC link voltage	900		V
V_{GES}		± 20		V
I_C	$T_s = 25 \text{ (70) }^\circ\text{C}$	400 (300)		A
Inverse diode				
$I_F = -I_C$	$T_s = 25 \text{ (70) }^\circ\text{C}$	400 (300)		A
I_{FSM}	$T_j = 150 \text{ }^\circ\text{C}, t_p = 10 \text{ ms; sin.}$	2880		A
I^2t (Diode)	Diode, $T_j = 150 \text{ }^\circ\text{C}, 10 \text{ ms}$	41		kA ² s
T_j (T_{stg})		- 40 (- 25) ... + 150 (125)		°C
V_{isol}	AC, 1 min. (main terminals to heat sink)	3000		V

Characteristics		$T_s = 25 \text{ }^\circ\text{C}$ unless otherwise specified		
Symbol	Conditions	min.	typ.	max.
IGBT				
V_{CEsat}	$I_C = 350 \text{ A}, T_j = 25 \text{ (125) }^\circ\text{C}$	2,6 (3,1)	3,1	V
V_{CEO}	$T_j = 25 \text{ (125) }^\circ\text{C}$	1,2 (1,3)	1,5 (1,6)	V
r_{CE}	$T_j = 25 \text{ (125) }^\circ\text{C}$	3,8 (5)	4,5 (5,8)	mΩ
I_{CES}	$V_{GE} = 0 \text{ V}, V_{CE} = V_{CES}, T_j = 25 \text{ (125) }^\circ\text{C}$	(20)	0,8	mA
$E_{on} + E_{off}$	$I_C = 350 \text{ A}, V_{CC} = 600 \text{ V}$		105	mJ
	$T_j = 125 \text{ }^\circ\text{C}, V_{CC} = 900 \text{ V}$		185	mJ
$R_{CC' + EE'}$	terminal chip, $T_j = 125 \text{ }^\circ\text{C}$	0,25		mΩ
L_{CE}	top, bottom	7,5		nH
C_{CHC}	per phase, AC-side	2,8		nF
Inverse diode				
$V_F = V_{EC}$	$I_F = 300 \text{ A}, T_j = 25 \text{ (125) }^\circ\text{C}$	2,1 (1,9)	2,6	V
V_{TO}	$T_j = 25 \text{ (125) }^\circ\text{C}$	1,3 (1)	1,4 (1,1)	V
r_T	$T_j = 25 \text{ (125) }^\circ\text{C}$	2,5 (3)	3,4 (3,9)	mΩ
E_{rr}	$I_C = 350 \text{ A}, V_{CC} = 600 \text{ V}$		12	mJ
	$T_j = 125 \text{ }^\circ\text{C}, V_{CC} = 900 \text{ V}$		15	mJ
Mechanical data				
M_{dc}	DC terminals, SI Units	6	8	Nm
M_{ac}	AC terminals, SI Units	13	15	Nm
w	SKiiP® 2 System w/o heat sink		1,9	kg
w	heat sink		4,7	kg
Thermal characteristics (P16 heat sink; 310 m³/h); "r" reference to temperature sensor				
$R_{th(j-s)I}$	per IGBT		0,064	K/W
$R_{th(j-s)D}$	per diode		0,188	K/W
$R_{th(s-a)}$	per module		0,043	K/W
Z_{th}	R_i (mK/W) (max. values)		$\tau_{ai}(s)$	
	1 2 3 4	1 2 3 4		
$Z_{th(j-r)I}$	7 50 8	1 0,13 0,001		
$Z_{th(j-r)D}$	21 144 23	1 0,13 0,001		
$Z_{th(r-a)}$	13,9 18,9 6,6 3,6	262 50 5 0,02		



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2-pack integrated gate driver

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Gate driver features

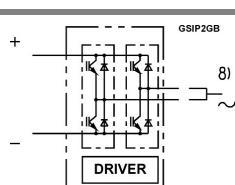
- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- Short circuit protection
- Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 68T.1 (climate) 25/85/56 (SKiiP® 2 gate driver)

Absolute Maximum Ratings		Values	Units
Symbol	Conditions		
V_{S1}	stabilized 15 V power supply	18	V
V_{S2}	unstabilized 24 V power supply	30	V
V_{iH}	input signal voltage (high)	15 + 0,3	V
dV/dt	secondary to primary side	75	kV/μs
V_{isolIO}	input / output (AC, r.m.s., 2s)	3000	Vac
V_{isol12}	output 1 / output 2 (AC, r.m.s., 2s)	1500	Vac
f_{max}	switching frequency	20	kHz
$T_{op} (T_{stg})$	operating / storage temperature	- 25 ... + 85	°C

Characteristics ($T_a = 25^\circ C$)				
Symbol	Conditions	min.	typ.	max.
V_{S1}	supply voltage stabilized	14,4	15	15,6
V_{S2}	supply voltage non stabilized	20	24	30
I_{S1}	$V_{S1} = 15 V$	$210+320*f/f_{max}+1,3*(I_{AC}/A)$		
I_{S2}	$V_{S2} = 24 V$	$160+220*f/f_{max}+1,0*(I_{AC}/A)$		
V_{iT+}	input threshold voltage (High)	11,2		V
V_{iT-}	input threshold voltage (Low)			5,4
R_{IN}	input resistance	10		kΩ
$t_{d(on)IO}$	input-output turn-on propagation time	1,2		μs
$t_{d(off)IO}$	input-output turn-off propagation time	1,6		μs
$t_{pERRRESET}$	error memory reset time	9		μs
t_{TD}	top / bottom switch : interlock time	3,3		μs
$I_{analogOUT}$	8 V corresponds to max. current of 15 V supply voltage (available when supplied with 24 V)	400		A
$I_{Vs1outmax}$	output current at pin 12/14	50		mA
I_{AOmax}	logic low output voltage	5		mA
V_{O1}	logic high output voltage	0,6		V
V_{OH}		30		V
I_{TRIPSC}	over current trip level ($I_{analog OUT} = 10 V$)	500		A
I_{TRIPLG}	ground fault protection	110		A
T_{tp}	over temperature protection	120		°C
U_{DCTRIP}	trip level of U_{DC} -protection ($U_{analog OUT} = 9 V$); (option)	900		V

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